

IN THE SPECIFICATION:

On page 2, please amend the last paragraph which continues on page 3 as follows:

B¹
A red-light-emitting semiconductor laser structure is usually a multilayer structure made up of quaternary mixed crystals $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ (where $0 \leq x \leq 1$ and $0 \leq y \leq 1$), which will be herein simply labeled as AlGaIP), which consist essentially of Al, Ga, In and P. And an infrared semiconductor laser structure is usually a multilayer structure made up of ternary mixed crystals $\text{Al}_z\text{Ga}_{1-z}\text{As}$ (where $0 \leq z \leq 1$), which will be herein simply labeled as AlGaAs), which consist essentially of Al, Ga and As.

On page 11, please amend the fourth paragraph as follows:

B²
In the inventive method for fabricating a semiconductor laser device, the etching control layer is preferably made of $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ (where $0 \leq x \leq 1$ and $0 \leq y \leq 1$) and the first multilayer structure preferably includes semiconductor layers made of $\text{Al}_z\text{Ga}_{1-z}\text{As}$ (where $0 \leq z \leq 1$).

On page 12, please amend the first paragraph as follows:

B³
In the inventive method for fabricating a semiconductor laser device, the etching control layer is preferably made of $\text{Al}_z\text{Ga}_{1-z}\text{As}$ (where $0 \leq z \leq 1$) and the first multilayer structure preferably includes semiconductor layers made of $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ (where $0 \leq x \leq 1$ and $0 \leq y \leq 1$).

On page 15, please amend the third paragraph as follows:

B⁴
In the inventive semiconductor laser device, the etching control layer is preferably made of $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ (where $0 \leq x \leq 1$ and $0 \leq y \leq 1$) and the first semiconductor laser structure preferably includes semiconductor layers made of $\text{Al}_z\text{Ga}_{1-z}\text{As}$ (where $0 \leq z \leq 1$).

On page 15, please amend the fifth paragraph which continues onto page 16 as follows:

B6
In the inventive semiconductor laser device, the etching control layer is preferably made of $\text{Al}_z\text{Ga}_{1-z}\text{As}$ (where $0 \leq z \leq 1$) and the first multilayer structure preferably includes semiconductor layers made of $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$ (where $0 \leq x \leq 1$ and $0 \leq y \leq 1$).